	Application No.	Applicant(s)	
Notice of Allowability	10/799,996 Examiner	BARNS ET AL.  Art Unit	
	- Zammo.	Acom	
	Lan Vinh	1765	
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R	(OR REMAINS) CLOSED in this ap or other appropriate communication IGHTS. This application is subject t	plication. If not included n will be mailed in due course. <b>THIS</b>	
1. This communication is responsive to <u>Amendment filed on the second of the second of</u>	<u>8/21/2006</u> .		
2.  The allowed claim(s) is/are <u>1,2,6-8 and 11-14</u> .			
3. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the:	nder 35 U.S.C. § 119(a)-(d) or (f).		
1. Certified copies of the priority documents have	e been received.		
2. Certified copies of the priority documents have	been received in Application No	·	
3. Copies of the certified copies of the priority do	• • • • • • • • • • • • • • • • • • • •		
International Bureau (PCT Rule 17.2(a)).		<b>3</b> • • • • • • • • • • • • • • • • • • •	
* Certified copies not received:			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	itted. Note the attached EXAMINER es reason(s) why the oath or declara	S AMENDMENT or NOTICE OF ation is deficient.	
5. CORRECTED DRAWINGS ( as "replacement sheets") mus	st be submitted.		
(a) ☐ including changes required by the Notice of Draftspers		·948) attached	
1) hereto or 2) to Paper No./Mail Date	•	,	
(b) including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the C	Office action of	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the	.84(c)) should be written on the drawi he header according to 37 CFR 1.121(	ngs in the front (not the back) of d).	
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATERIAL r FOR THE DEPOSIT OF BIOLOGIC	must be submitted. Note the AL MATERIAL.	
Attachment(s)	5 <b>- N</b> orth (1.6 1.5		
1. Notice of References Cited (PTO-892)	_	Patent Application (PTO-152)	
<ol> <li>Notice of Draftperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/0</li> </ol>	Paper No./Mail Da	<ol> <li>Interview Summary (PTO-413),</li> <li>Paper No./Mail Date</li> <li>⊠ Examiner's Amendment/Comment</li> </ol>	
Paper No./Mail Date 4.  Examiner's Comment Regarding Requirement for Deposit		ent of Reasons for Allowance	
of Biological Material	9.	$\mathcal{O}(\mathcal{O}_{\mathcal{A}})$	
		Lan Vinh AU 1765	

## **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

On page 1 of the specification, "This application is a continuation of 10/008,683 filed on 12/04/2001 now US Patent 6,743,683" has been inserted below "Polysilicon opening polish"

## Allowable Subject Matter

2. Claims 1-2, 6-8,11-14 allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claim 1, the cited prior art of record fails to disclose a method for fabricating a semiconductor structure comprises the step of forming a top layer comprises TiN after forming the dielectric layer and removing a portion of the top layer before removing the portion of the dielectric layer, in combination with the rest of the limitations of claim 1. The closest cited prior art of Buynoski (US 6,194,299) discloses a method for fabricating of a low resistivity MOSFET comprises the step of forming a top layer 205 of photoresist after forming the dielectric layer 204 and removing a portion of the top layer before removing the portion of the dielectric layer (col 3, lines 50-53., fig.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## **Conclusion**

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LV

August 28, 2006